



Bipolar PNP Bare Die – BTP124

Part Description

The BTP124 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications.

Key Parameters:

- VCBO = -80V
- VCEO = -80V
- VEBO = -5V
- hFE = 56-777 @ VCE = -3V, IC = -0.1A
- VCE(Sat) = -0.4V @ IC = -0.5A, IB = -50mA
- fT = 100 MHz @ VCE = -10V, IE = 0A
- COBO = 20pF @ VCB = -10V

Features

Low VCE(sat)

Die Size (Unawn)

790µm X 790µm, 31 Mils X 31 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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